

# SHINDENGEN

## VX-2 Series Power MOSFET

N-Channel Enhancement type

**2SK2189  
(F10W50VX2)**

**500V 10A**

### FEATURES

- Input capacitance ( $C_{iss}$ ) is small.  
Especially, input capacitance at 0 bias is small.
- The static  $R_{ds(on)}$  is small.
- The switching time is fast.

### APPLICATION

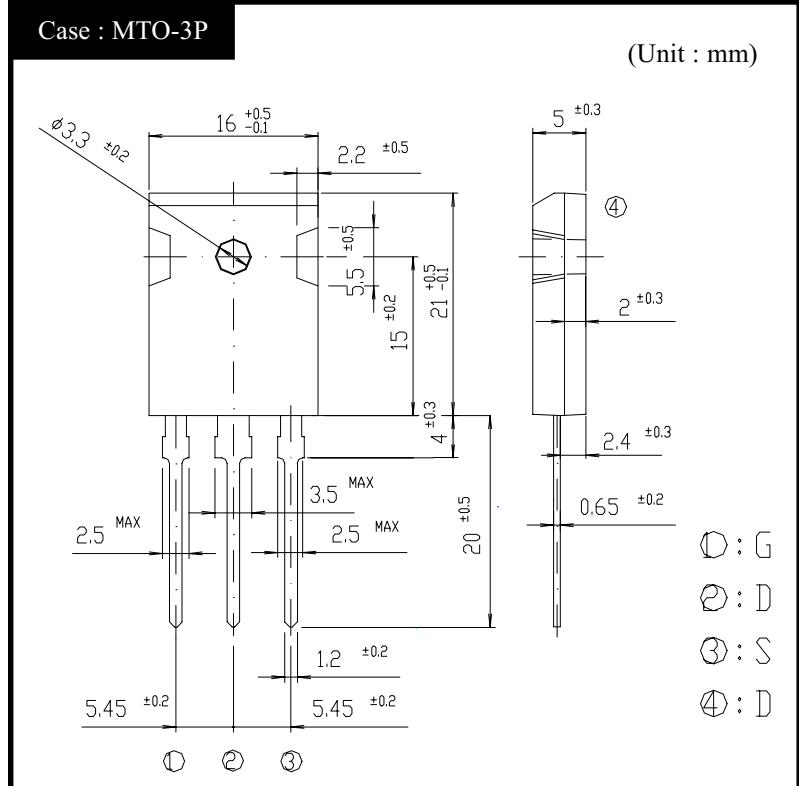
- Switching power supply of AC 100V input
- High voltage power supply
- Inverter

### RATINGS

#### ● Absolute Maximum Ratings ( $T_c = 25^\circ\text{C}$ )

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	$T_{stg}$		-55~150	$^\circ\text{C}$
Channel Temperature	$T_{ch}$		150	
Drain-Source Voltage	$V_{DSS}$		500	V
Gate-Source Voltage	$V_{GSS}$		$\pm 30$	
Continuous Drain Current(DC)	$I_D$		10	A
Continuous Drain Current(Peak)	$I_{DP}$		30	
Continuous Source Current(DC)	$I_S$		10	
Total Power Dissipation	$P_T$		70	W
Single Pulse Avalanche Current	$I_{AS}$	$T_{ch} = 25^\circ\text{C}$	10	A
Mounting Torque	$T_{OR}$	( Recommended torque : 0.5N·m )	0.8	N·m

### OUTLINE DIMENSIONS

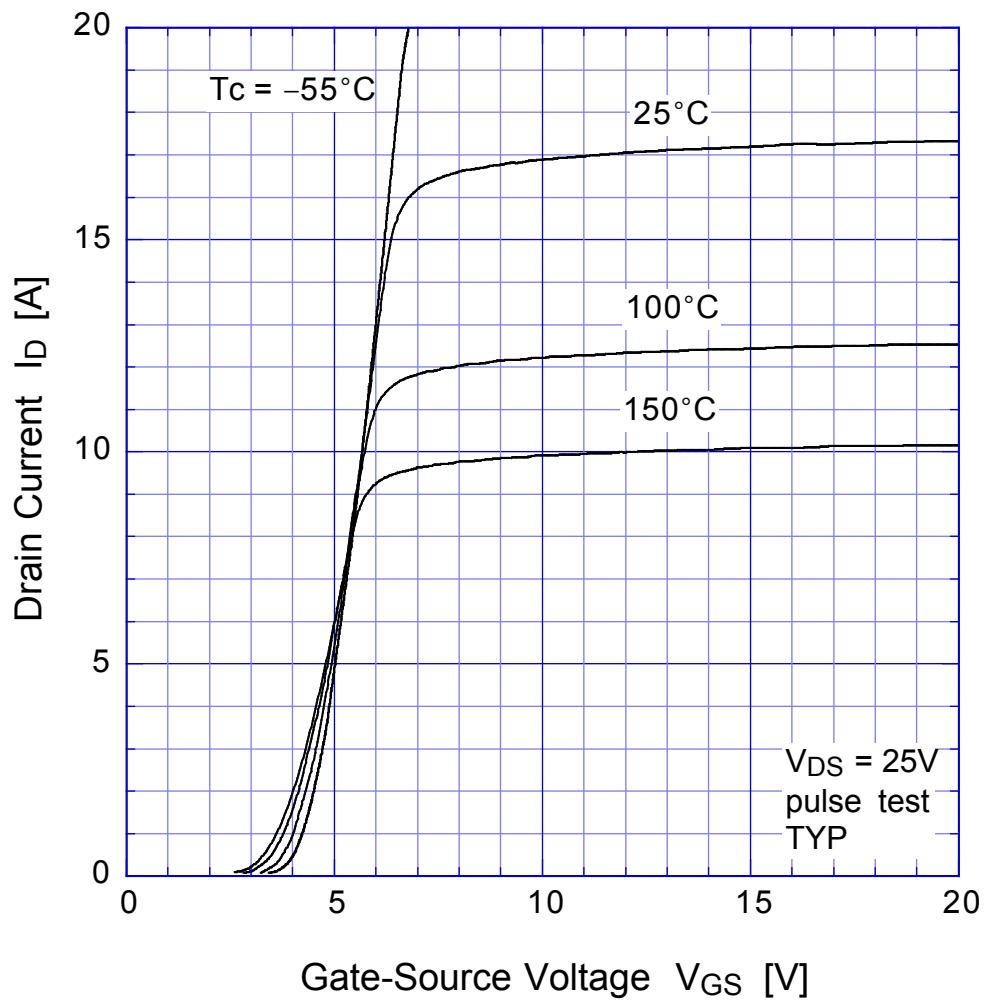


●Electrical Characteristics T<sub>c</sub> = 25°C

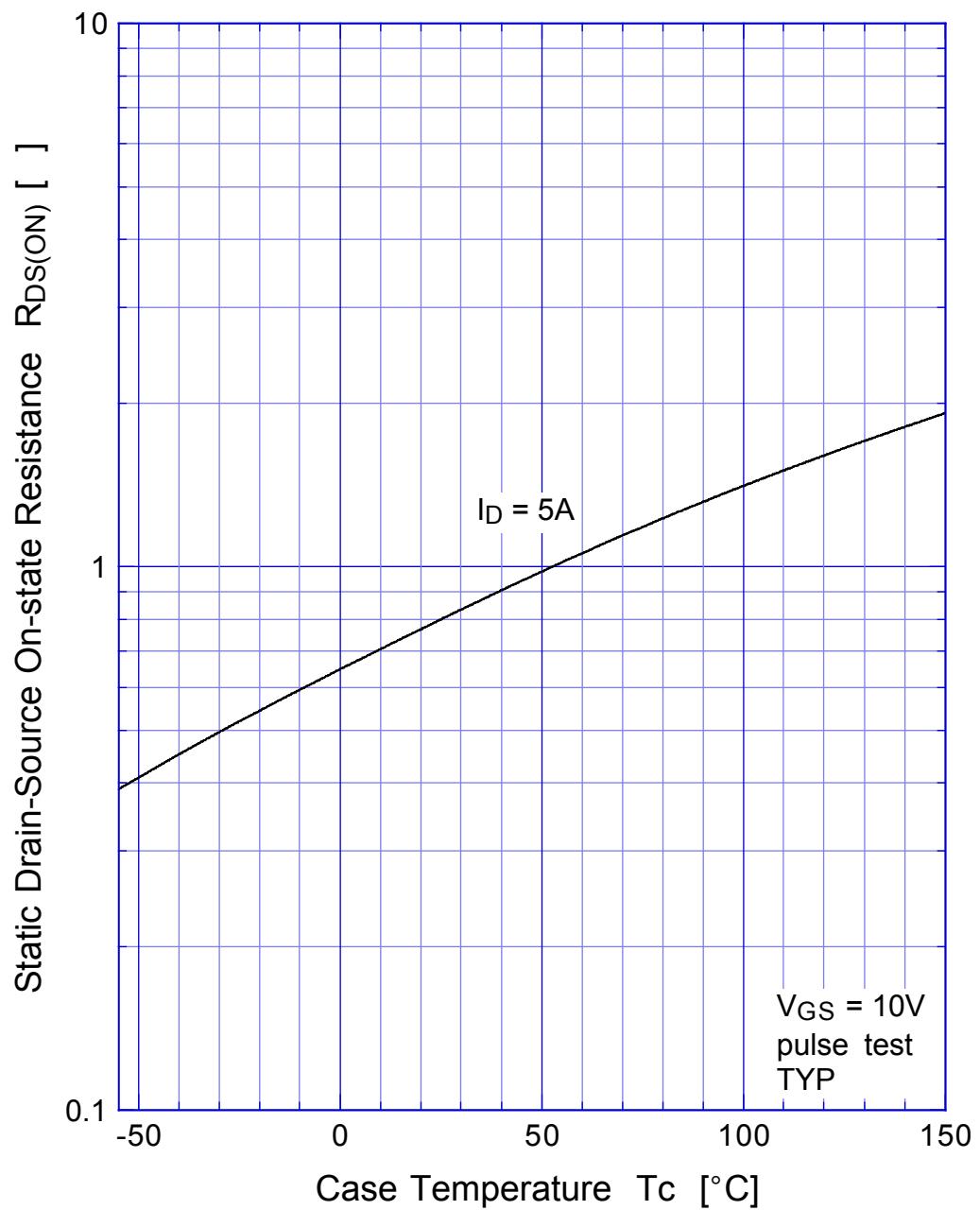
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	ID = 1mA, V <sub>GS</sub> = 0V	500			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 500V, V <sub>GS</sub> = 0V			250	μA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V			±0.1	
Forward Transconductance	g <sub>s</sub>	ID = 5A, V <sub>DS</sub> = 10V	2.4	6.3		S
Static Drain-Source On-state Resistance	R <sub>DSON</sub>	ID = 5A, V <sub>GS</sub> = 10V		0.8	1.0	Ω
Gate Threshold Voltage	V <sub>TH</sub>	ID = 1mA, V <sub>DS</sub> = 10V	2.5	3.0	3.5	V
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 5A, V <sub>GS</sub> = 0V			1.5	
Thermal Resistance	θ <sub>jc</sub>	junction to case			1.78	°C/W
Total Gate Charge	Q <sub>g</sub>	V <sub>DD</sub> = 400V, V <sub>GS</sub> = 10V, ID = 10A		30		nC
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHz		890		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			70		
Output Capacitance	C <sub>oss</sub>			200		
Turn-On Time	t <sub>on</sub>	ID = 5A, V <sub>GS</sub> = 10V, R <sub>L</sub> = 30Ω		70	110	ns
Turn-Off Time	t <sub>off</sub>			140	220	

# 2SK2189

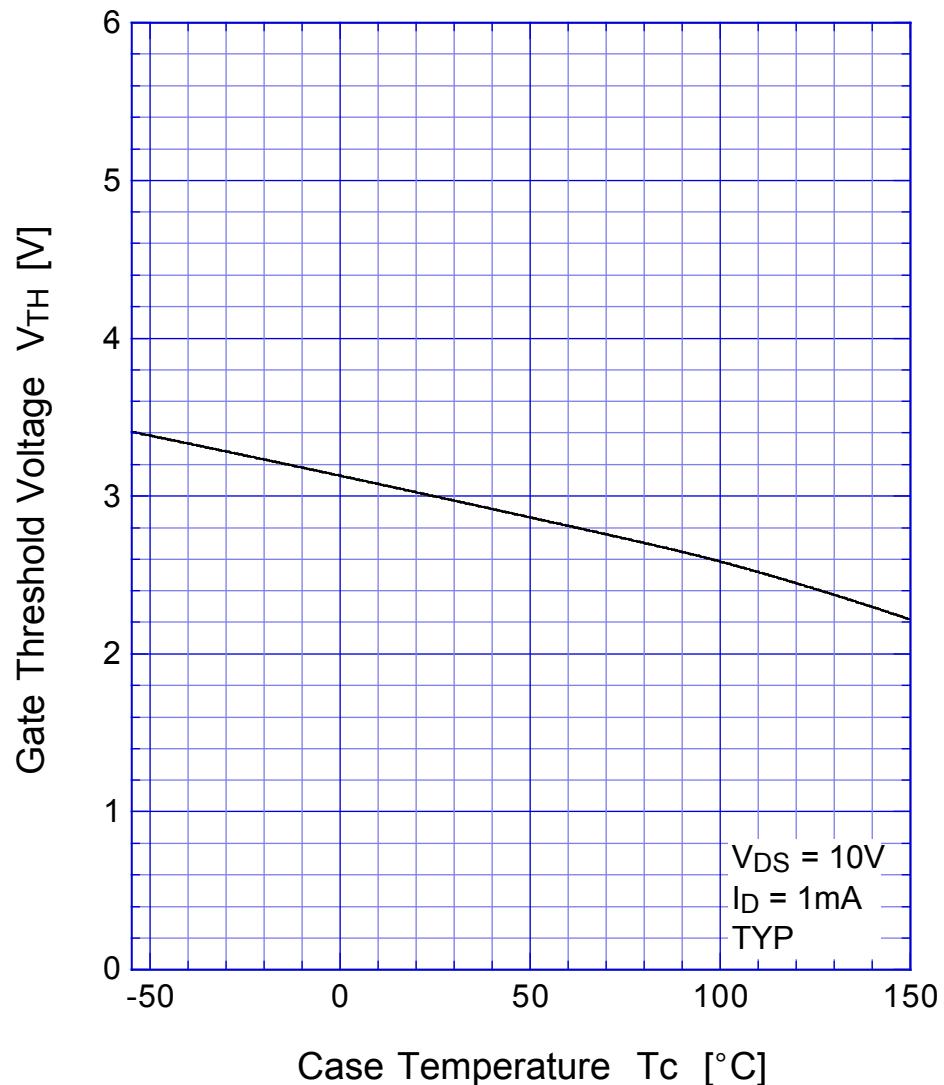
## Transfer Characteristics



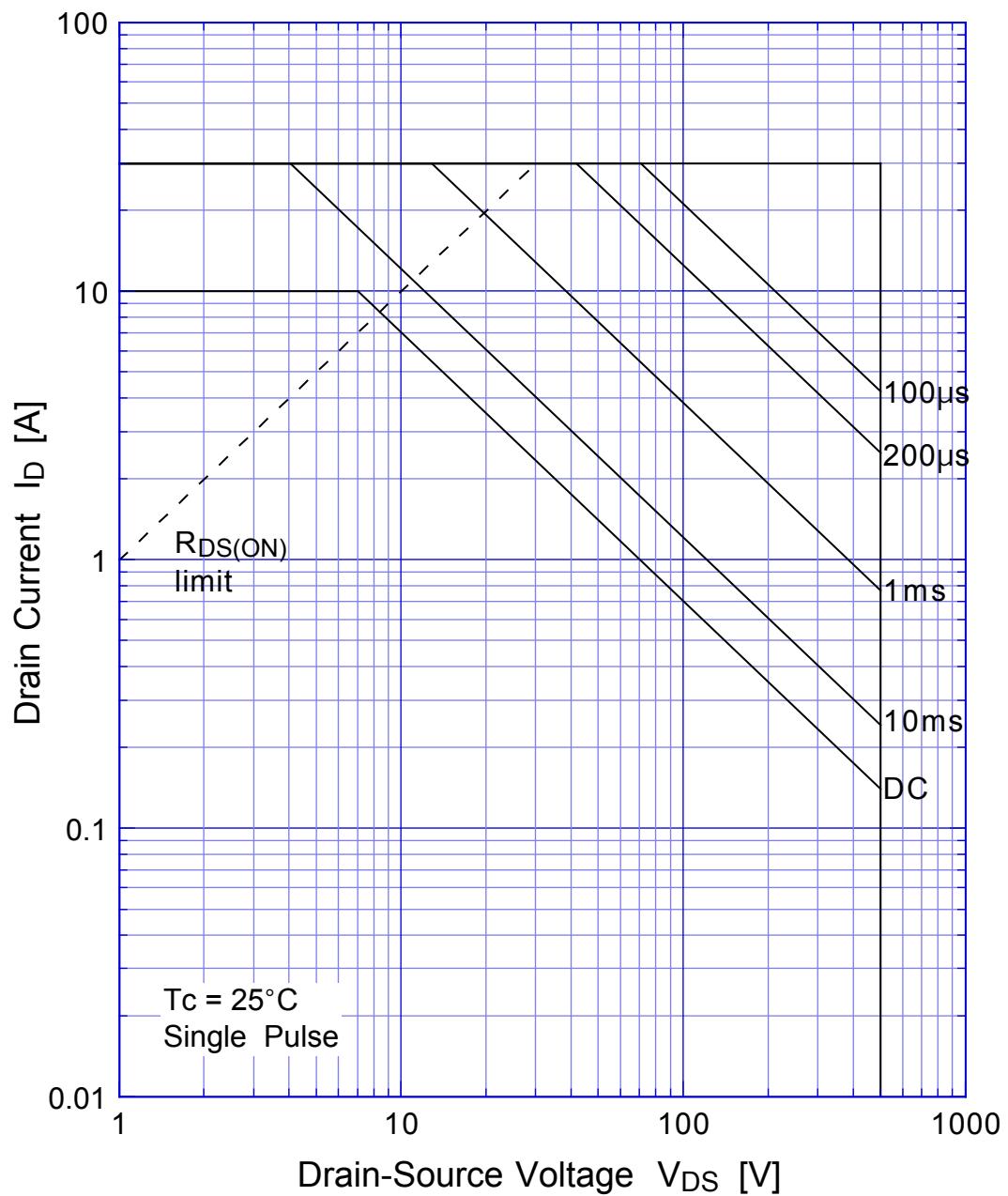
## **2SK2189 Static Drain-Source On-state Resistance**



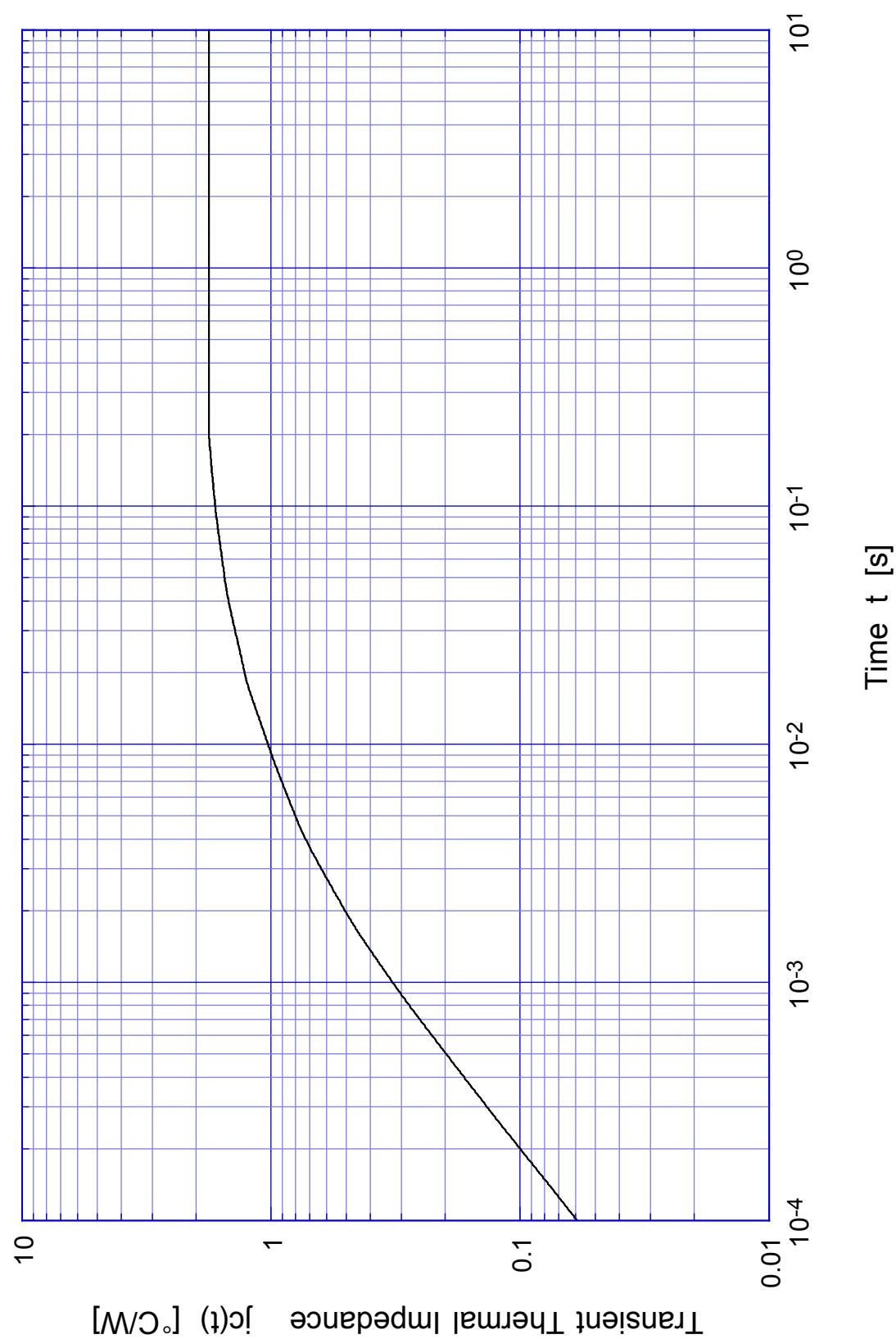
## **2SK2189      Gate Threshold Voltage**



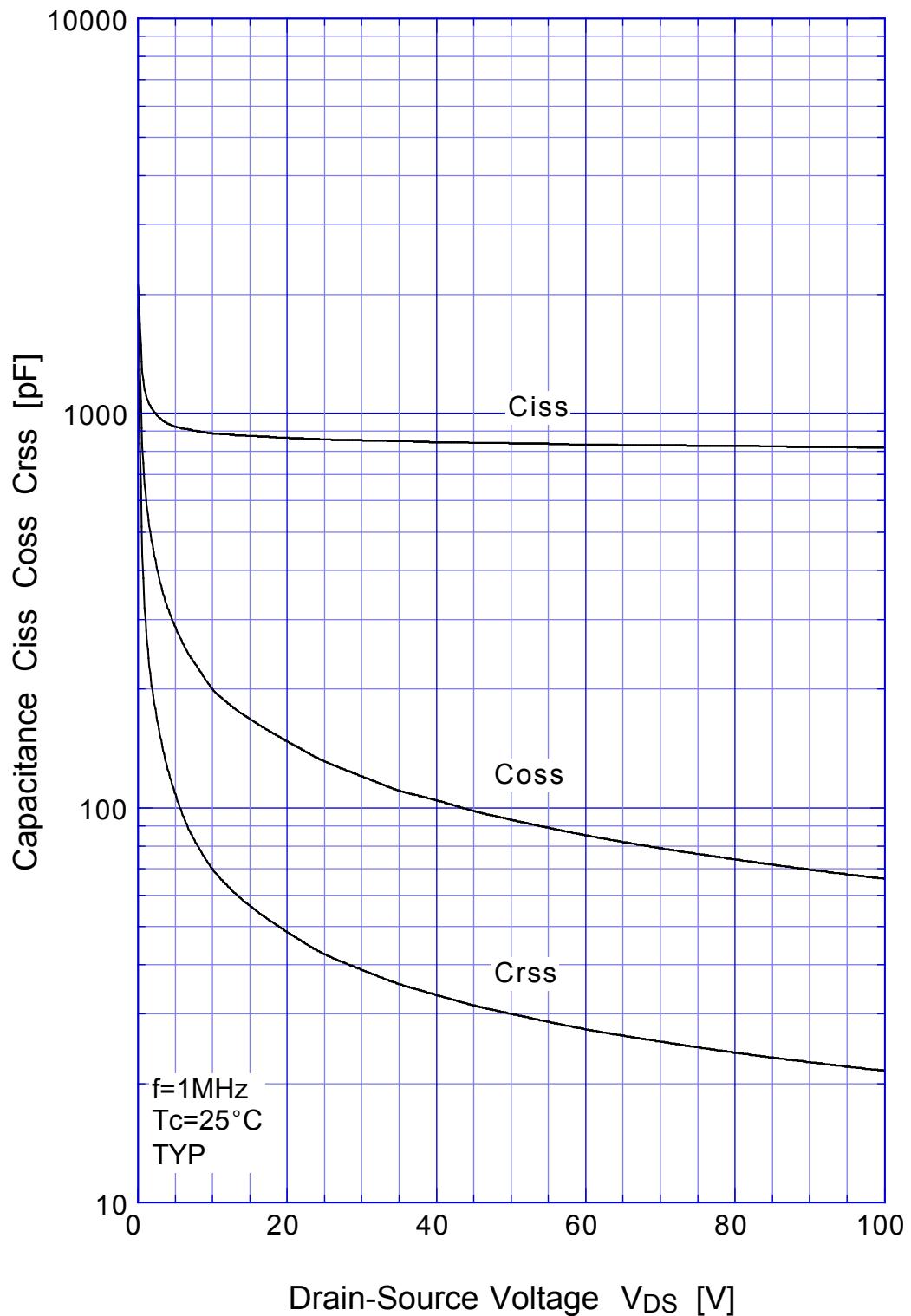
## 2SK2189 Safe Operating Area



## 2SK2189 Transient Thermal Impedance

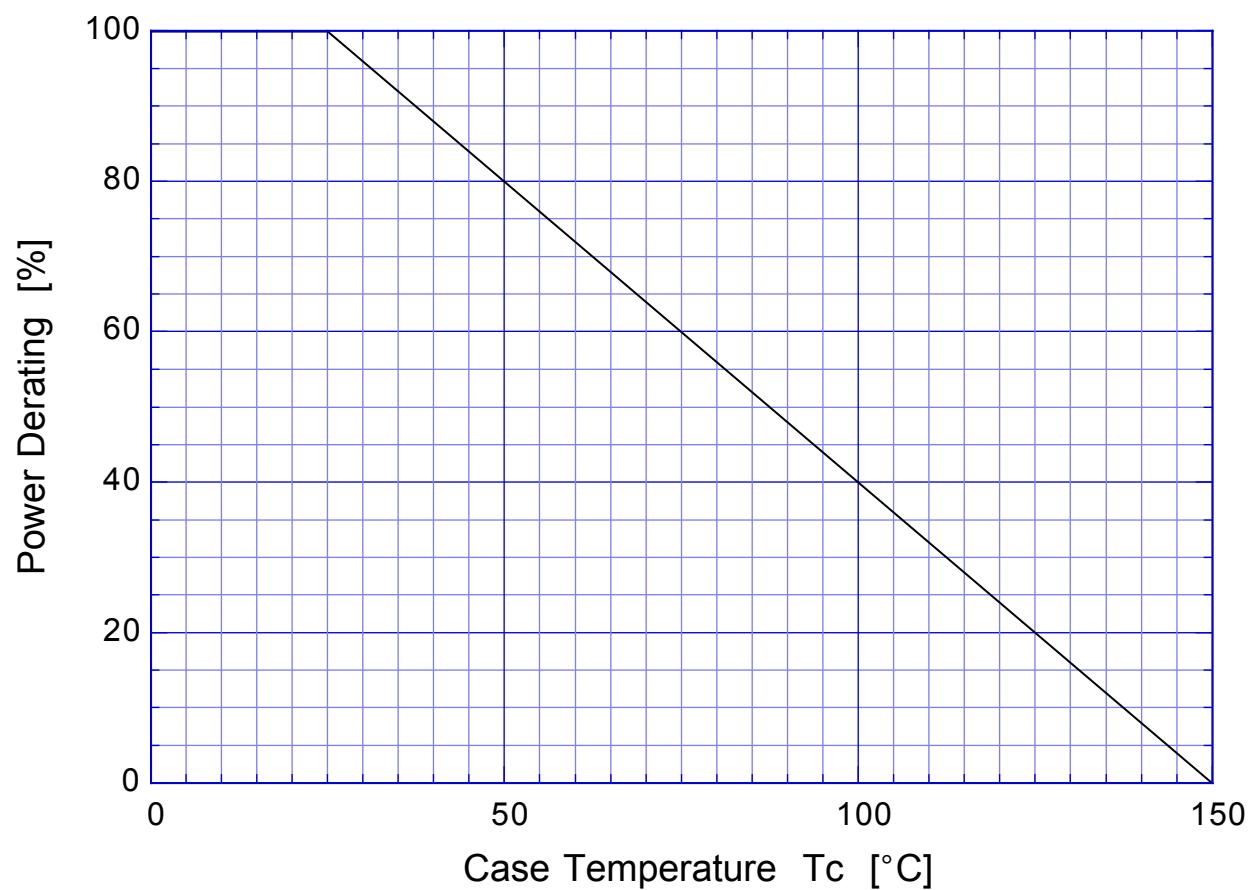


2SK2189 Capacitance



**2SK2189**

Power Derating



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### Gate Charge Characteristics

